

AMENDMENTS TO THE CLAIMS

1-11. (Cancelled)

12. (Currently Amended): A method for forming a pattern over a substrate, comprising:

providing a master having at least one opening

providing a substrate having an etching layer formed thereon, the etching layer having at least one stepped portion;

placing the master over the etching layer, the opening of the master being corresponding to the etching region to be etched;

providing a resist supplying roll of which a surface being coated with a resist;

contacting and rotating the resist supplying roll on the master to fill the resist in the at least one opening of the master on the etching layer having at least one stepped portion, the master being separated from the substrate at a distance;

hardening the filled resist in the at least one opening of the master by applying ~~a heat or~~ an ultraviolet ray to the resist;

forming a resist pattern on the etching layer by separating the master from the substrate; and

etching the etching layer using the resist pattern as a mask,

wherein the master is separated from the substrate by a few micrometers (μm) during filling the resist in opening of the master ~~and the master is separated from the hardened resist without any outer impact,~~

~~wherein the resist pattern is contacted with the upper surface of the etching layer,~~

wherein the resist coated on the surface of the supplying roll is directly filled in at least one opening of the master.

13-17. (Cancelled)

18. (Previously Presented) The method of claim 12, wherein the master is separated from the substrate by 1-9 μm during filling the resist in opening of the master.

19. (Previously Presented) The method of claim 12, the master is separated from the substrate by several micrometers (μm) during filling the resist in opening of the master.